

 **Active**

2 L2: (165) ((twir \$3 near bond\$3) near 12 crack) and (reflect\$3 near 3 (layer film))) ((twir \$3 n

L4 (3) -2001015671-

15-0184143.pn

Failed

 Saved

8916) ((multilevel\$2 multi\$3 adj level\$2 multilayer\$2 multi\$3 adj layer\$2) adj (intercon

278544 ((multilevel\$2 multi\$3 adj level\$2 multilayer\$2 multi\$3 adj layer\$2))

3450401) interconnect\$4 (inter adj. connect\$4) wiring metal metalization metallization

3446454) interconnect\$4 (inter adj connect\$4) wiring metal meta??ization

☛ (2847046) pad contact

🐦 (7344860) (open \$5 via hole aperture trench groove well cavity)

2 (253431) (pad contact) near 2 ((open \$5 via hole aperture trench groove well cavity))

31765) (interconnect\$4 (inter adj connect\$4) wiring metal meta??ization) near9 ((pad c

☛ (1888) (257/758) CCLS

```

(613) (interconnect$4 (inter-adj connect$4) wiring metal meta??ization ) near0 (pad con

```

6110 ((interconnect\$4 (inter adj connect\$4) wiring metal meta??ization) near0 ((pad co

3 (172) (((Interconnect\$4 (Inter adj connect\$4) wiring metal meta??ization) near0 ((pad con

```

(111) (((interconnect$4 (inter adj connect$4) wiring metal meta??ization ) near0 (pad con

```

```

(10) (((interconnect$4 (inter adj connect$4) wiring metal meta??ization ) near8 (pad con

```

329 (((interconnect\$4 (inter adj connect\$4) wiring metal meta??ization) near9 ((pad con

✎ (279801) (insula1\$5 dielectric) near layer

15085) (insulating dielectric) near layer

(58) (((interconnect\$4 (inter adj connect\$4) wiring metal meta??ization) near9 (pad con

[illegible]

 BGS form
 LSAR form
 Image
 Text
 HTML

U	I	Inventor	Document ID	Issue D Pa	Title	Current O	Current X Ref	Retrieval Cl	S	C	P	2	3	4	5	6	Image Doc. D	P
---	---	----------	-------------	------------	-------	-----------	---------------	--------------	---	---	---	---	---	---	---	---	--------------	---

NOGUCHI, J et al	JP 11145288 A	200405/80	Insulating film structure for copper wiring in semicond	US 6184143
------------------	---------------	-----------	---	------------

Ohashi, Naofumi US 6184143 B 200102-80 Semiconductor integrated circuit device and fabricati 438/697 257/E21.58 F F F F F F F US 6184143

















